

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1695	136/244.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/03 15:21
L2	1315	257/431.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/03 15:21
L3	1908	257/431.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/03 15:21
L4	2089	136/244.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/03 15:21
L5	293	257/464.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/03 15:22
L6	1179	257/461.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/03 15:22
L7	269174	((solar near (cell battery)) photovoltaic photodiode photoresistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 15:22
L8	3494	(I1 I2 I3 I4 I5 I6) and I7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 15:23

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L9	49	l8 and (porous pore porosity) with (silicon \$2S!)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 15:24
L10	7	l8 and (porous pore porosity) with (silicon \$2S!) with (thick\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 15:25
L11	9	l8 and ((porous pore porosity) with thick\$5) same (silicon \$2S!)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 15:31
L17	56	((bilyalov near renat) (ulyashin near alexander) (poortmans near jef) (fahner near wolfgang)).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:26
L18	22	l17 and porous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:26
L19	1236	136/246.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:36
L20	959	136/255.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:36

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L21	2496	136/258.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:36
L22	1064	136/259.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:36
L23	934	136/261.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:37
L24	104	(I19 I20 I21 I22 I23) and (porous pore porosity) with (silicon \$2SI))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/03 18:37
S1	11	136/244.ccls. and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	OFF	2007/06/03 15:01
S2	25	257/431.ccls. and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	OFF	2007/06/03 15:02
S3	3	257/464.ccls. and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	OFF	2007/06/03 15:02
S4	9	257/461.ccls. and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	OFF	2007/06/03 15:02
S5	2471	"257"/\$.ccls. and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	OFF	2007/06/03 15:04
S6	2474	"257"/\$.ccls. and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/03 15:05
S7	441	S6 and ((solar near (cell battery)) photovoltaic photodiode photoresistor)	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/03 15:05

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S8	926	((solar near (cell battery))) photovoltaic photodiode photoresistor) and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/03 15:06
S9	131	"136"/\$.ccls. and (porous near (semiconductor (Si silicon)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/03 15:06

## EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L12	85393	((solar near (cell battery))) photovoltaic photodiode photoresistor)	USPAT; UPAD	OR	ON	2009/12/03 18:11
L13	6069	("I1" "I2" "I3" "I4" "I5" "I6") and "I7"	USPAT; UPAD	OR	ON	2009/12/03 18:11
L14	18	"I8" and (porous pore porosity) with (silicon \$2SI)	USPAT; UPAD	OR	ON	2009/12/03 18:11
L15	2	"I8" and (porous pore porosity) with (silicon \$2SI) with (thick\$5)	USPAT; UPAD	OR	ON	2009/12/03 18:12
L16	741	((solar near (cell battery))) photovoltaic photodiode photoresistor) and (porous near (semiconductor (Si silicon)))	USPAT; UPAD	OR	ON	2009/12/03 18:12
L25	1085	136/244.ccls.	USPAT; UPAD	OR	OFF	2009/12/03 18:43
L26	981	257/431.ccls.	USPAT; UPAD	OR	OFF	2009/12/03 18:43
L27	1085	136/244.ccls.	USPAT; UPAD	OR	OFF	2009/12/03 18:44
L28	928	257/461.ccls.	USPAT; UPAD	OR	OFF	2009/12/03 18:44
L29	928	257/461.ccls.	USPAT; UPAD	OR	OFF	2009/12/03 18:44
L30	781	136/246.ccls.	USPAT; UPAD	OR	ON	2009/12/03 18:44
L31	660	136/255.ccls.	USPAT; UPAD	OR	ON	2009/12/03 18:44
L32	1387	136/258.ccls.	USPAT; UPAD	OR	ON	2009/12/03 18:45
L33	642	136/259.ccls.	USPAT; UPAD	OR	ON	2009/12/03 18:45
L34	522	136/261.ccls.	USPAT; UPAD	OR	ON	2009/12/03 18:45
L35	42	(I25 I26 I27 I28 I29 I30 I31 I32 I33 I34) and porous near (silicon \$2SI)	USPAT; UPAD	OR	ON	2009/12/03 18:46

### EAST Search History (Interference)

L36	224	257/464.ccls.	USPAT; UPAD	OR	ON	2009/12/03 18:50
L37	2	l36 and porous near (silicon \$2Si!)	USPAT; UPAD	OR	ON	2009/12/03 18:50